

Corrections to High Efficiency Tandem Organic Light Emitting Diode Using Organic Heterojunction as Charge Generation Layer: An Investigation into Charge Generation Model and Device Performance

Hengda Sun, Qingxun Guo, Dezhi Yang, Yonghua Chen, Jiangshan Chen, and Dongge Ma*

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The structure description in the article may cause some confusion for some punctuation mistakes, therefore, an errata is given in the following:

On page 272, row 1, the current text is “ITO and MoO₃ (3 nm) with 20 wt % MoO₃; TAPC (50 nm), HTM (15 nm), and HAT-CN (15 nm) with 3 wt % Cs; and BPhen (50 nm), CS (1 nm), and Al (100 nm)”.

The corrected text is as follows: “ITO (170 nm)/MoO₃ (3 nm)/20 wt % MoO₃:TAPC (50 nm)/HTM (15 nm)/HAT-CN (15 nm)/3 wt % Cs:BPhen (50 nm)/Cs (1 nm)/Al (100 nm)”.

On page 272, row 2, the current text is “(Device A): ITO (170 nm) and MoO₃ (3 nm) with 25 wt % MoO₃; TAPC (50 nm) and TAPC (10 nm) with 8 wt % Ir(ppy)₂(acac); TCTA (6 nm) with 8 wt % Ir(ppy)₂(acac); BPhen (8 nm) and BPhen (10 nm) with 3 wt % Cs; BPhen (35 nm), HAT-CN (15 nm) and m-MTDATA (15 nm) with 25 wt % MoO₃; TAPC (35 nm) and TAPC (10 nm) with 8 wt % Ir(ppy)₂(acac); TCTA (6 nm) with 8 wt % Ir(ppy)₂(acac); BPhen 8% (8 nm) and BPhen (10 nm) with 3 wt % Cs; and BPhen (45 nm), Cs (1 nm), and Al (100 nm)”.

The corrected text is as follows: “(Device A): ITO (170 nm)/MoO₃ (3 nm)/25 wt % MoO₃:TAPC (50 nm)/TAPC (10 nm)/8 wt % Ir(ppy)₂(acac):TCTA (6 nm)/8 wt % Ir(ppy)₂(acac):BPhen (8 nm)/BPhen (10 nm)/3 wt % Cs:BPhen (35 nm)/HAT-CN (15 nm)/m-MTDATA (15 nm)/25 wt % MoO₃:TAPC (35 nm)/TAPC (10 nm)/8 wt % Ir(ppy)₂(acac):TCTA (6 nm)/8 wt % Ir(ppy)₂(acac):BPhen (8 nm)/BPhen (10 nm)/3 wt % Cs:BPhen (45 nm)/Cs (1 nm)/Al (100 nm)”.

On page 272, row 2, the current text is “(Device B): ITO (170 nm) and MoO₃ (3 nm) with 25 wt % MoO₃; TAPC (50 nm) and TAPC (10 nm) with 8 wt % Ir(ppy)₂(acac); TCTA (6 nm) with 8 wt % Ir(ppy)₂(acac); BPhen (8 nm) and BPhen (10 nm) with 3 wt % Cs; BPhen (45 nm), Cs (1 nm), and Al (100 nm)”.

The corrected text is as follows: “(Device B): ITO (170 nm)/MoO₃ (3 nm)/25 wt % MoO₃:TAPC (50 nm)/TAPC (10 nm)/8 wt % Ir(ppy)₂(acac):TCTA (6 nm)/8 wt % Ir(ppy)₂(acac):BPhen (8 nm)/BPhen (10 nm)/3 wt % Cs:BPhen (45 nm)/Cs (1 nm)/Al (100 nm)”.

On page 275, row 1, the current text is “we fabricated the following device: ITO and MoO₃ (3 nm) with 20 wt % MoO₃; TAPC (50 nm), m-MTDATA (15 nm), and HAT-CN (15 nm) with 3 wt % Cs; and BPhen (50 nm), Cs (1 nm), and Al (100 nm; device C)”.

The corrected text is as follows: “we fabricated the following (Device C): ITO (170 nm)/MoO₃ (3 nm)/20 wt %

MoO₃:TAPC (50 nm)/m-MTDATA (15 nm)/HAT-CN (15 nm)/3 wt % Cs:BPhen (50 nm)/Cs (1 nm)/Al (100 nm)”.

On page 275, row 1, the current text is “a device with only m-MADATA between the charge transport layers is prepared: ITO and MoO₃ (3 nm) with 20 wt % MoO₃; TAPC (50 nm) and m-MADATA (15 nm) with 3 wt % Cs; and BPhen (50 nm), CS (1 nm), and Al (100 nm; device D)”.

The corrected text is as follows: “a device with only m-MADATA between the charge transport layers is prepared (Device D): ITO (170 nm)/MoO₃ (3 nm)/20 wt % MoO₃:TAPC (50 nm)/m-MTDATA (15 nm)/3 wt % Cs:BPhen (50 nm)/Cs (1 nm)/Al (100 nm)”.

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